

URFP064 Preliminary Power MOSFET

70A, 60V N-CHANNEL POWER MOSFET

■ DESCRIPTION

The UTC **URFP064** is an N-channel enhancement power MOSFET using UTC's advanced technology to provide the customers with a minimum on-state resistance and high switching speed.

1 TO-247

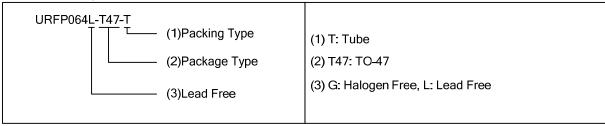
■ FEATURES

- * $R_{DS(ON)}$ <20m Ω @ V_{GS} =10V, I_D =70A
- * High Switching Speed

ORDERING INFORMATION

Ordering	Daelsage	Pin Assignment			Doolsing	
Lead Free	Halogen Free	Package	1	2	3	Packing
URFP064L-T47-T	URFP064G-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source



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ABSOLUTE MAXIMUM RATINGS

PARA	AMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I _D	70	
	Pulsed (Note 2)	I _{DM}	280	A
Avalanche Current		I _{AR}	70	Α
Single Pulsed Avalanche Energy		E _{AS}	1000	mJ
Power Dissipation		P_D	190	W
Junction Temperature		TJ	-55~+150	°C
Storage Temperature		T _{STG}	-55~+150	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. L = 69mH, I_{AS} = 70A, V_{DD} = 25V, R_{G} = 25 Ω

■ ELECTRICAL CHARACTERISTICS

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS		OTMBOL	, including the second	10		11111 0 1	0.4
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA				V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =60V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+20V			+100	nA
	Reverse		V _{GS} =-20V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	I _D =250μA	2		4	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =70A			20	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}			7400		pF
Output Capacitance Reverse Transfer Capacitance		Coss	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		3200		pF
		C_{RSS}			540		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V _{DD} =50V, V _{GS} =10V,			190	nC
Gate to Source Charge		Q_GS	I _D =1.3A, I _D =100μA,			55	nC
Gate to Drain Charge		Q_GD				90	nC
Turn-ON Delay Time		$t_{D(ON)}$			21		ns
Rise Time		t_R	V _{DD} =30V, I _D =70A,		190		ns
Turn-OFF Delay Time		t _{D(OFF)}	R _G =25Ω, V _{GS} =0~10V		110		ns
Fall-Time		t_{F}			190		ns
SOURCE- DRAIN DIODE RATIN	IGS AND	CHARACTE	RISTICS				
Maximum Body-Diode Continuous Current		Is				70	Α
Maximum Body-Diode Pulsed Current		I _{SM}				280	Α
Drain-Source Diode Forward Voltage		V_{SD}	I _S =70A			1.28	V

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